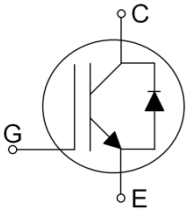
1200V Field Stop Trench Technology
High Speed Switching
Low Conduction Loss
Positive Temperature Coefficient
Easy parallel Operation
RoHS compliant
JEDEC Qualification



Applications :
Induction Heating, Soft switching application, UPS, Welder, Inverter

Device	Package	Marking	Remark
TGL40N120FD	TO-264	TGL40N120FD	RoHS

Absolute Maximum Ratings

Parameter		Symbol	Value	Unit
Collector-Emitter Voltage		V_{CES}	1200	V
Gate-Emitter Voltage		V_{GES}	20	V
Continuous Collector Current	T_C = 25	I_c	80	A
	T_C = 100		40	A
Pulsed Collector Current (Note 1)		I_{CM}	120	A
Diode Continuous Forward Current	T_C = 100	I_F	40	A
Diode Maximum Forward Current		I_{FM}	120	A
Power Dissipation	T_C = 25	P_D	480	W
	T_C = 100		192	W
Operating Junction Temperature		T_J	-55 ~ 150	
Storage Temperature Range		T_{STG}	-55 ~ 150	
Maximum lead temperature for soldering purposes, □		T_L	300	

Thermal Characteristics

Parameter	Symbol	Value	Unit
Maximum Thermal resistance, Junction-to-Case	$R_{\theta JC}$ (IGBT)	0.26	/W
Maximum Thermal resistance, Junction-to-Case	$R_{\theta JC}$ (DIODE)	0.95	/W
Maximum Thermal resistance, Junction-to-Ambient	$R_{\theta JA}$	25	/W

Electrical Characteristics of the IGBT T_C=25 , unless otherwise noted

Parameter	Symbol	Test condition	Min.	Typ.	Max.	Unit
OFF						
Collector Emitter Breakdown Voltage	BV_{CES}	V_{GE} = 0V, I_C = 1mA	1200	--	--	V
Zero Gate Voltage Collector Current	I_{CES}	V_{CE} = 1200V, V_{GE} = 0V	--	--	1	mA
Gate Emitter Leakage Current	I_{GES}	V_{CE} = 0V, V_{GE} = ± 20V	--	--	± 250	nA
ON						
Gate Emitter Threshold Voltage	$V_{GE(TH)}$	V_{GE} = V_{CE}, I_C = 40mA	4.5	6.5	8.5	V
Collector Emitter Saturation Voltage	$V_{CE(SAT)}$	V_{GE} = 15V, I_C = 40A, T_C = 25 °C	--	2.0	2.6	V
		V_{GE} = 15V, I_C = 40A, T_C = 125 °C	--	2.45	--	V
DYNAMIC						
Input Capacitance	C_{IES}	V_{CE} = 30V, V_{GE} = 0V f = 1MHz	--	5150	--	pF
Output Capacitance	C_{OES}		--	150	--	pF
Reverse Transfer Capacitance	C_{RES}		--	100	--	pF
SWITCHING (Note 2)						
Turn-On Delay Time	$t_{d(on)}$	V_{CC} = 600V, I_C = 40A R_G = 5 , V_{GE} = 15V Inductive Load, T_C = 25 °C	--	55	--	ns
Rise Time	t_r		--	80	--	ns
Turn-Off Delay Time	$t_{d(off)}$		--	200	--	ns
Fall Time	t_f		--	55	110	ns
Turn-On Switching Loss	E_{ON}		--	5.3	8.0	mJ
Turn-Off Switching Loss	E_{OFF}		--	1.1	1.6	mJ
Total Switching Loss	E_{TS}		--	6.4	9.6	mJ
Turn-On Delay Time	$t_{d(on)}$	V_{CC} = 600V, I_C = 40A R_G = 5 , V_{GE} = 15V Inductive Load, T_C = 125 °C	--	45	--	ns
Rise Time	t_r		--	75	--	ns
Turn-Off Delay Time	$t_{d(off)}$		--	210	--	ns
Fall Time	t_f		--	115	--	ns
Turn-On Switching Loss	E_{ON}		--	5.6	8.4	mJ
Turn-Off Switching Loss	E_{OFF}		--	2.2	3.3	mJ
Total Switching Loss	E_{TS}		--	7.8	11.7	mJ
Total Gate Charge	Q_g	V_{CC} = 600V, I_C = 40A V_{GE} = 15V	--	320	480	nC
Gate-Emitter Charge	Q_{ge}		--	40	60	nC
Gate-Collector Charge	Q_{gc}		--	150	225	nC

Parameter	Symbol	Test condition		Min.	Typ.	Max.	Unit
Diode Forward Voltage	V_{FM}	I_F = 40A	T_C = 25 °C	--	2.85	--	V
			T_C = 125 °C	--	2.9	--	
Reverse Recovery Time	t_{rr}	I_F = 40A, di/dt = 200A/μs	T_C = 25 °C	--	200	--	ns
			T_C = 125 °C	--	325	--	
Reverse Recovery Current	I_{rr}		T_C = 25 °C	--	23	--	A
			T_C = 125 °C	--	43	--	
Reverse Recovery Charge	Q_{rr}		T_C = 25 °C	--	2500	--	

IGBT Characteristics

Fig. 1 Output characteristics

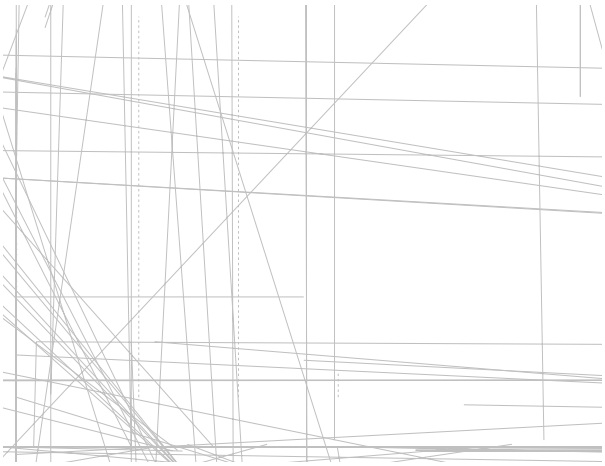


Fig. 2 Saturation voltage characteristics

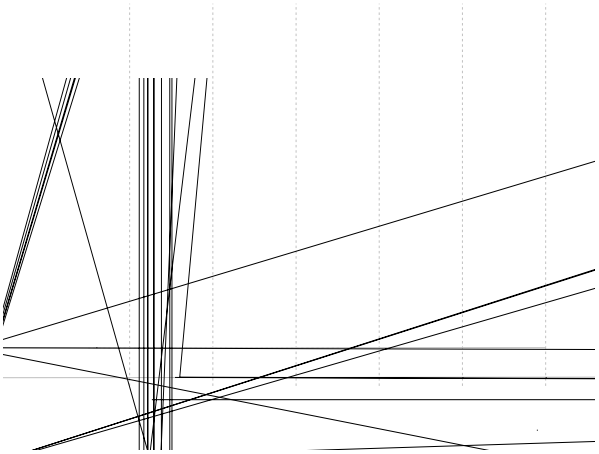


Fig. 3 Saturation voltage vs. collector current

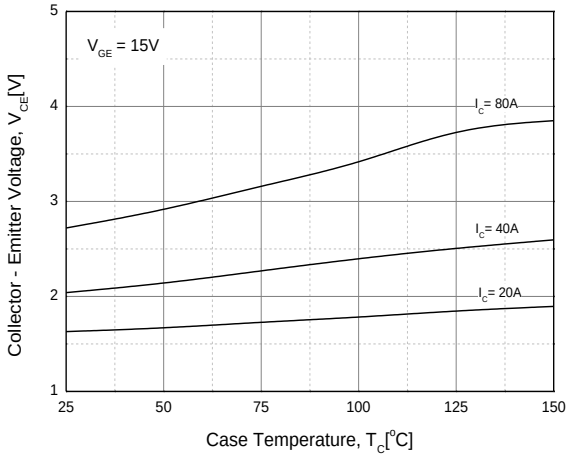


Fig. 4 Saturation voltage vs. gate bias

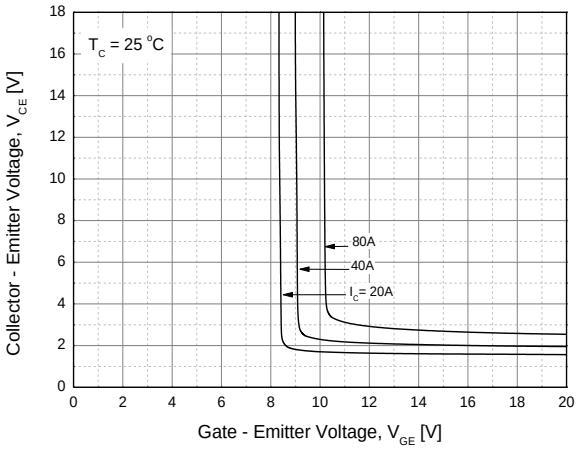


Fig. 5 Saturation voltage vs. gate bias

Fig. 6 Capacitance characteristics

IGBT Characteristics

Fig. 7 Turn-on time vs. gate resistor

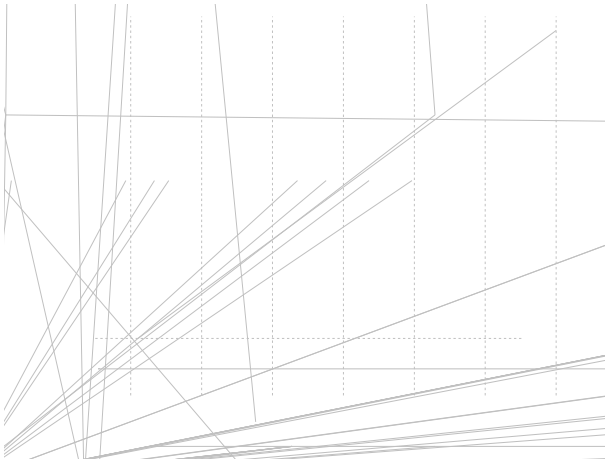


Fig. 8 Turn-off time vs. gate resistor

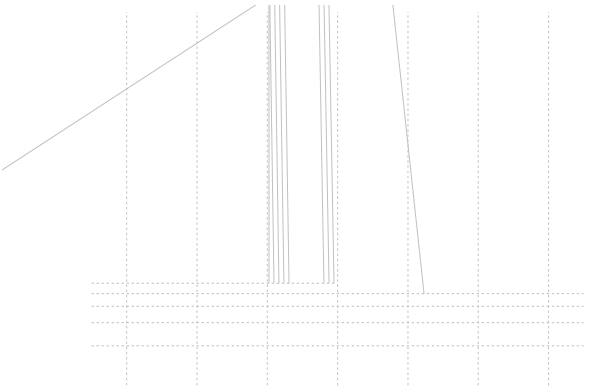


Fig. 9 Switching loss vs. gate resistor

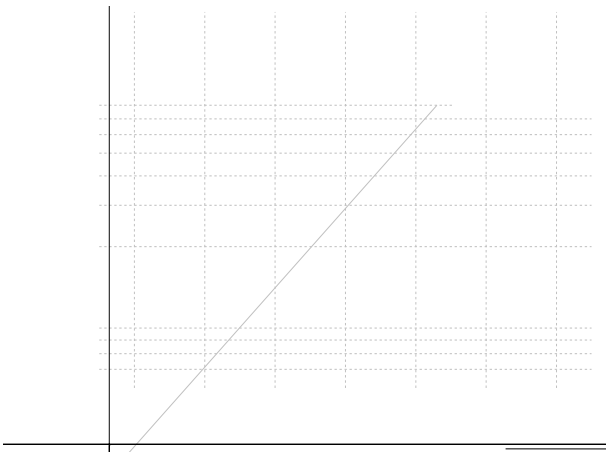


Fig. 10 Turn-on time vs. collector current

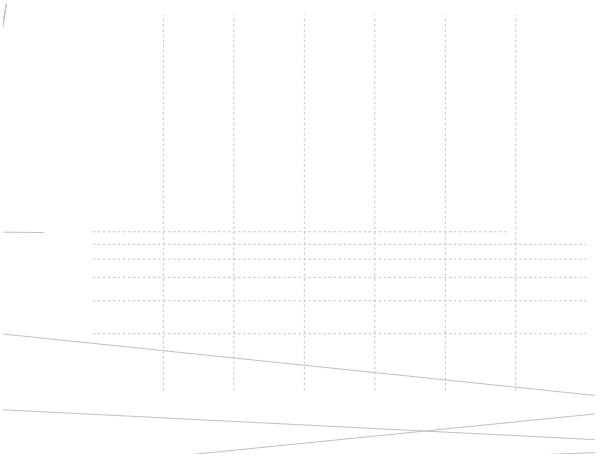


Fig. 11 Turn-off time vs. collector current

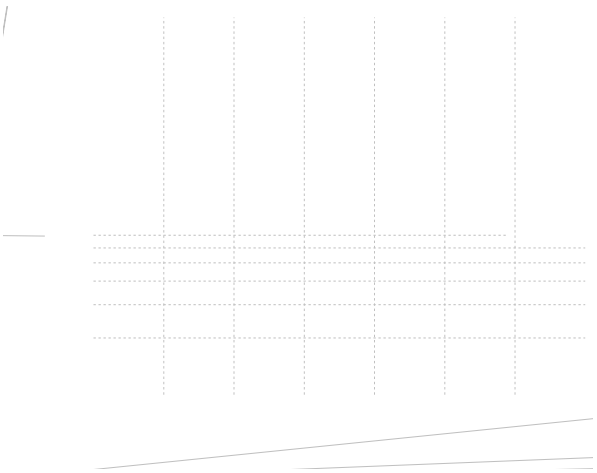
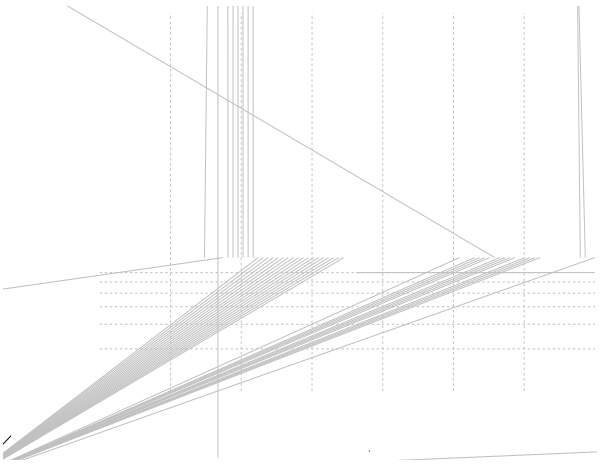


Fig. 12 Switching loss vs. collector current



IGBT Characteristics

Fig. 13 Gate charge characteristics

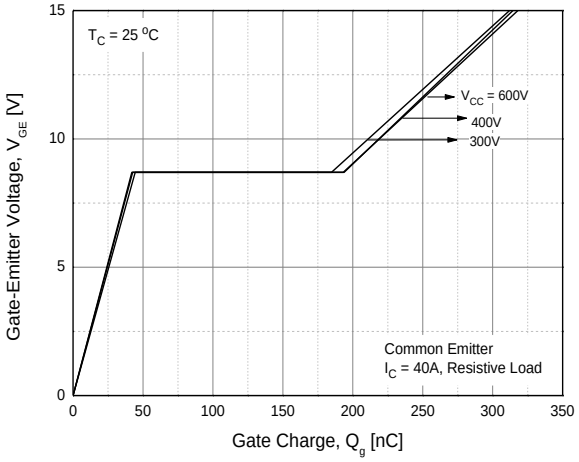


Fig. 14 SOA

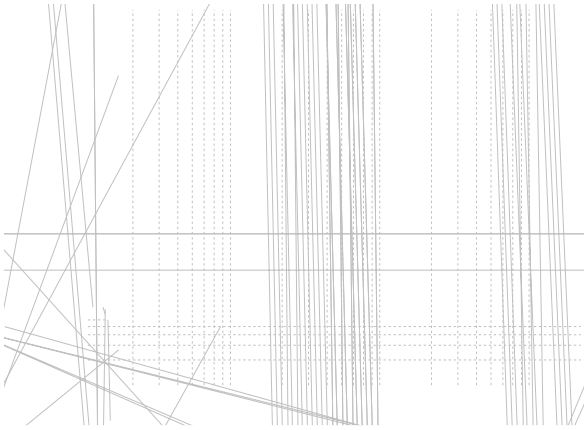


Fig. 15 RBSOA

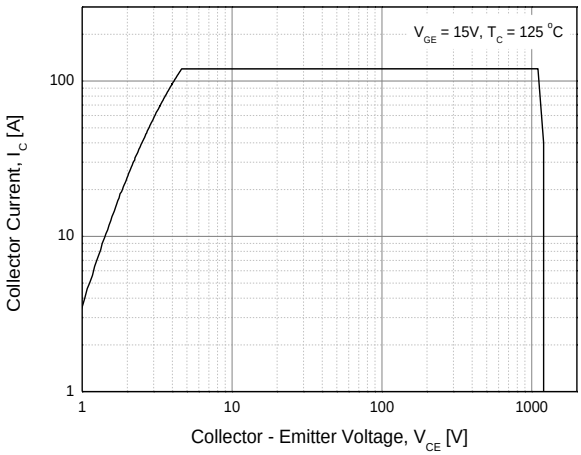


Fig. 16 Transient thermal impedance of IGBT

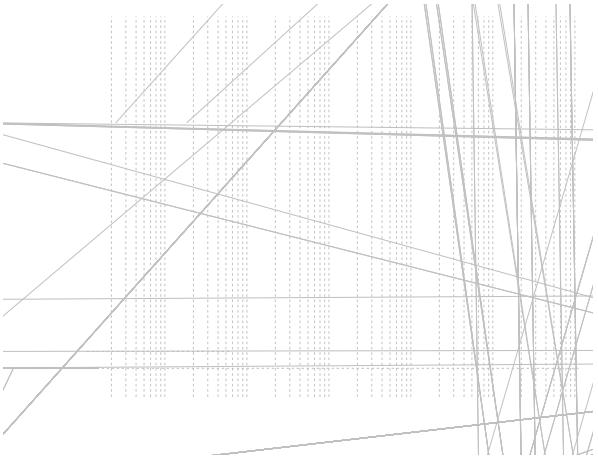
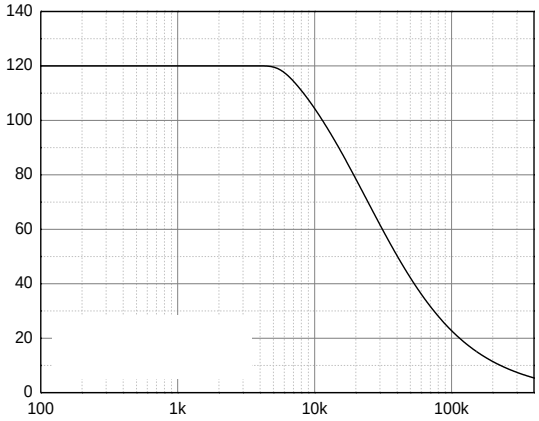


Fig. 17 Load Current vs. Frequency



Diode Characteristics

Fig. 18 Conduction characteristics

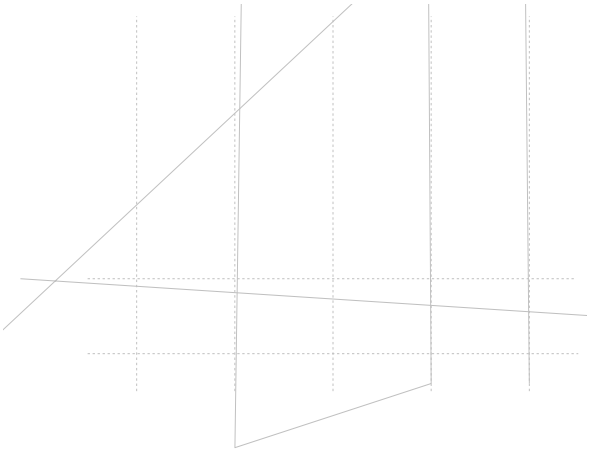


Fig. 19 Reverse recovery current vs. forward current

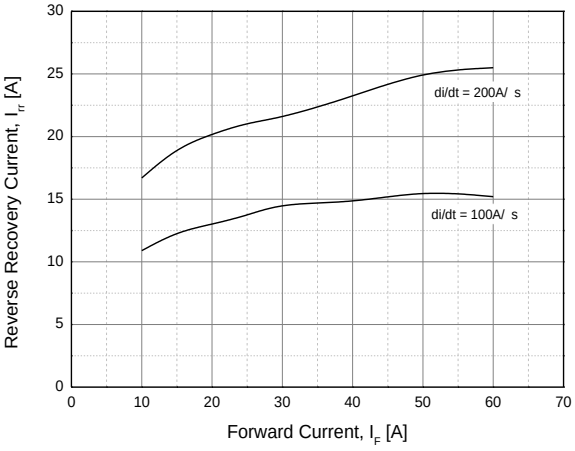


Fig. 20 Reverse recovery charge vs. forward current

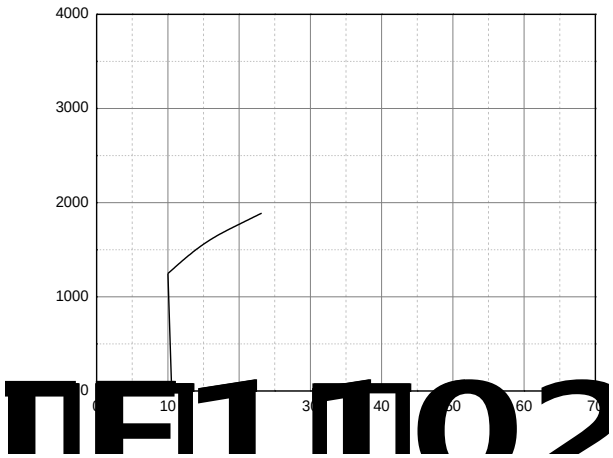
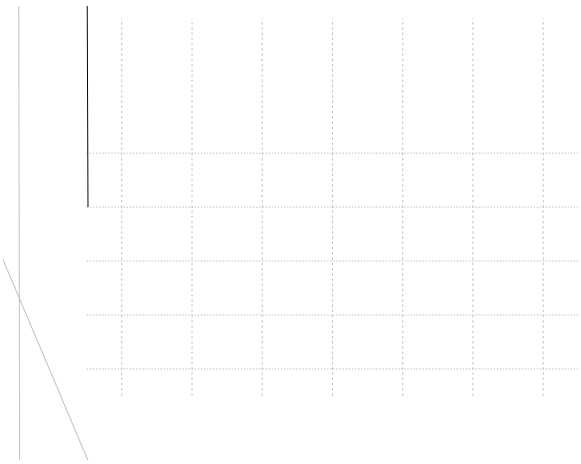
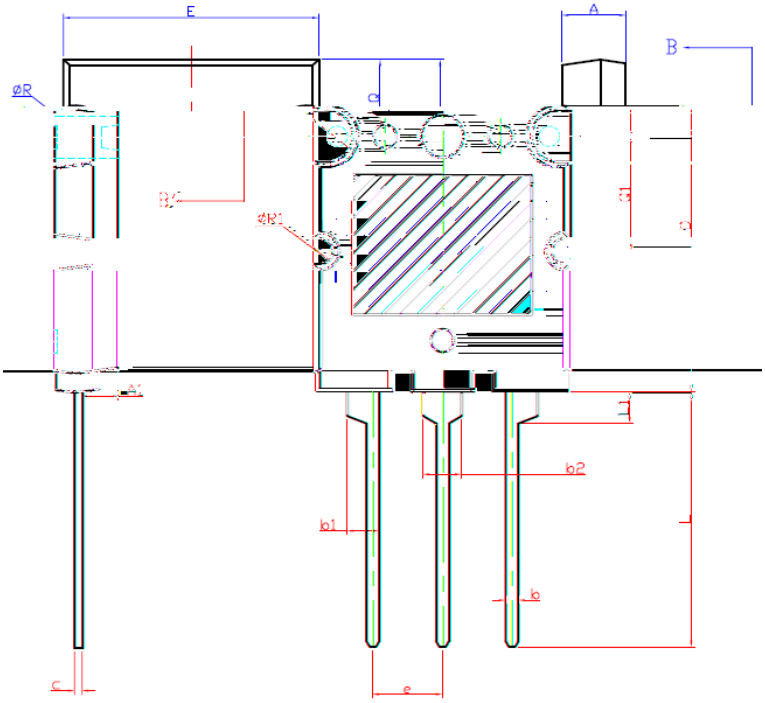
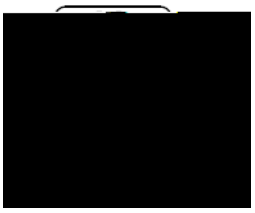


Fig. 21 Reverse recovery time vs. forward current

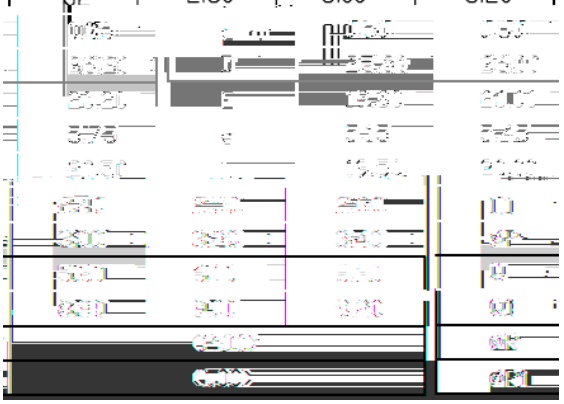


TO-264 MECHANICAL DATA





SYMBOL	MIN	NOM	MAX
A	4.80	5.00	5.20
A1	2.50	2.80	3.10
b	0.90	1.00	1.25
b1	2.30	2.50	2.70
b2	2.80	3.00	3.20



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